

November 2013

FQPF9P25

P-Channel QFET® MOSFET

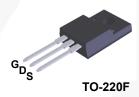
-250 V, -6 A, 620 mΩ

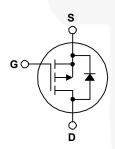
Description

This P-Channel enhancement mode power MOSFET is \bullet -6 A, -250 V, $R_{DS(on)}$ = 620 m Ω (Max.) @ V_{GS} = -10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance • Low Crss (Typ. 27 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, • 100% Avalanche Tested DC motor control, and variable switching power applications.

Features

- $I_{D} = -3 A$
- Low Gate Charge (Typ. 29 nC)





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQPF9P25	Unit	
V _{DSS}	Drain-Source Voltage		-250	V	
I _D	Drain Current - Continuous (T _C = 25°C)		-6.0	А	
	- Continuous (T _C = 100°C)		-3.9	Α	
I _{DM}	Drain Current - Pulsed	Note 1)	-24	А	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy (N		650	mJ	
I _{AR}	Avalanche Current	Note 1)	-6.0	А	
E _{AR}	Repetitive Avalanche Energy		5.0	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		-5.5	V/ns	
P_{D}	Power Dissipation (T _C = 25°C)		50	W	
	- Derate above 25°C		0.4	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
T _L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.		300	°C	

Thermal Characteristics

Symbol	Parameter	FQPF9P25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF9P25	FQPF9P25	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Uni
Off Cha	racteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-250			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-0.2		V/°C
I _{DSS}	Zara Oata Valtaria Busin Ouront	V _{DS} = -250 V, V _{GS} = 0 V			-1	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = -200 V, T _C = 125°C			-10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = 30 V, V _{DS} = 0 V		-	100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-3.0		-5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -3.0 A		0.48	0.62	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = -40 \text{ V}, I_{D} = -3.0 \text{ A}$		4.8		S
Dynami	ic Characteristics					
C _{iss}	Input Capacitance	V _{DS} = -25 V, V _{GS} = 0 V,	\	910	1180	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		170	220	pF
C _{rss}	Reverse Transfer Capacitance			27	35	рF
Switchi	ng Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = -125 V, I _D = -9.4 A,		20	50	ns
t _r	Turn-On Rise Time	$R_{\rm G} = 25 \Omega$		150	310	ns
t _{d(off)}	Turn-Off Delay Time			45	100	ns
t _f	Turn-Off Fall Time	(Note 4)		65	140	ns
Qg	Total Gate Charge	V _{DS} = -200 V, I _D = -9.4 A,		29	38	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V	/	7.6		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	/	14	-	nC
Drain-S	ource Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				-6.0	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F	Forward Current			-24	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -6.0 A			-5.0	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = -9.4 A,		190		ns
Q _{rr}	Reverse Recovery Charge	$dI_{\rm F}$ / $dt = 100 \text{A/}\mu\text{s}$		1.45		μС

- 1. Repetitive rating : pulse-width limited by maximum junction temperature.
- 2. L = 28.9 mH, I $_{AS}$ = -6.0 A, V $_{DD}$ = -50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C. 3. I $_{SD}$ ≤ -9.4 A, di/dt ≤ 300 A/ μ s , V $_{DD}$ ≤ BV $_{DSS}$, starting T $_{J}$ = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

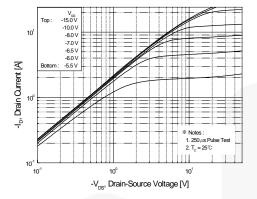


Figure 1. On-Region Characteristics

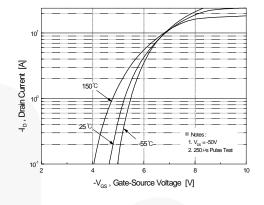


Figure 2. Transfer Characteristics

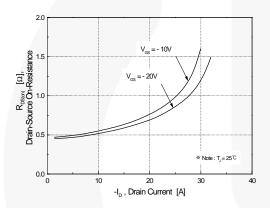


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

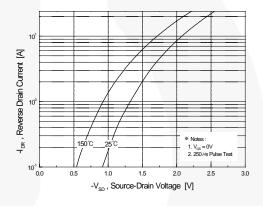


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

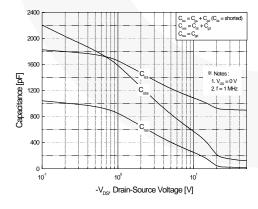


Figure 5. Capacitance Characteristics

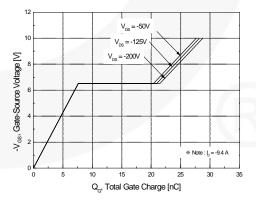
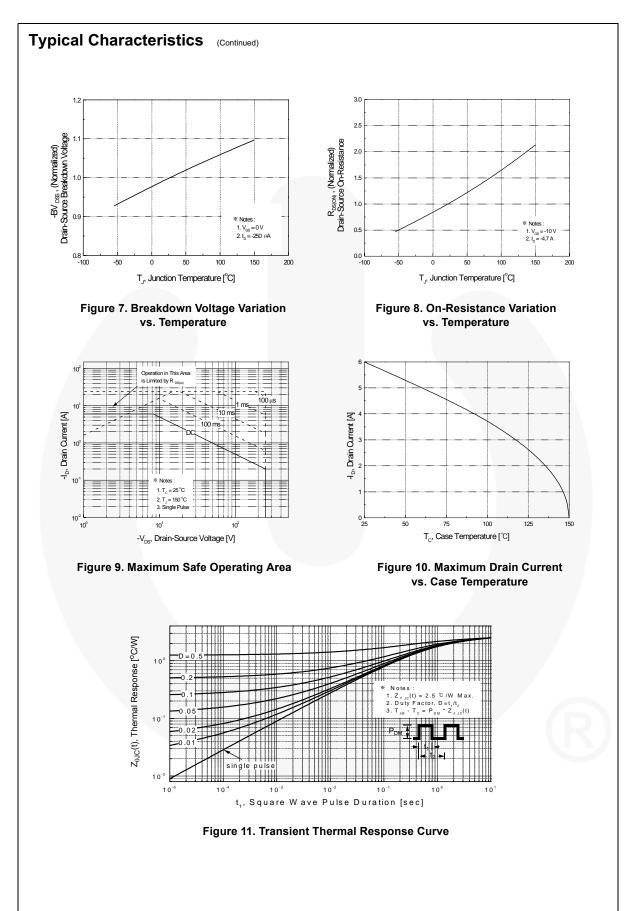


Figure 6. Gate Charge Characteristics



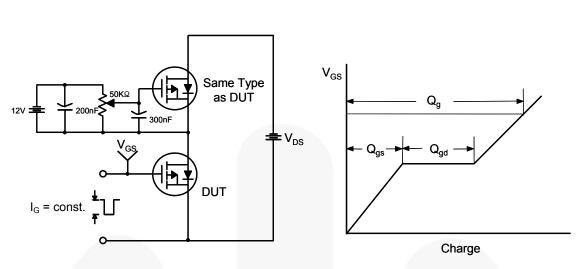


Figure 12. Gate Charge Test Circuit & Waveform

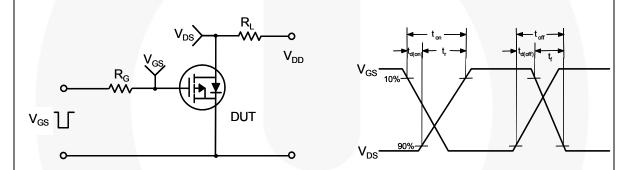


Figure 13. Resistive Switching Test Circuit & Waveforms

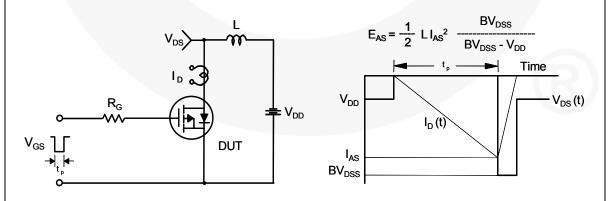
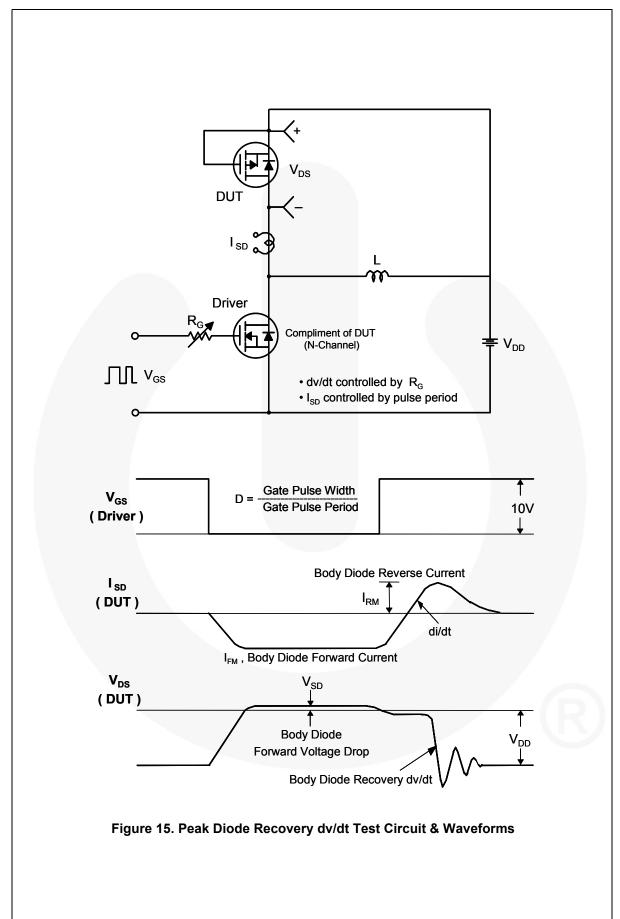


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

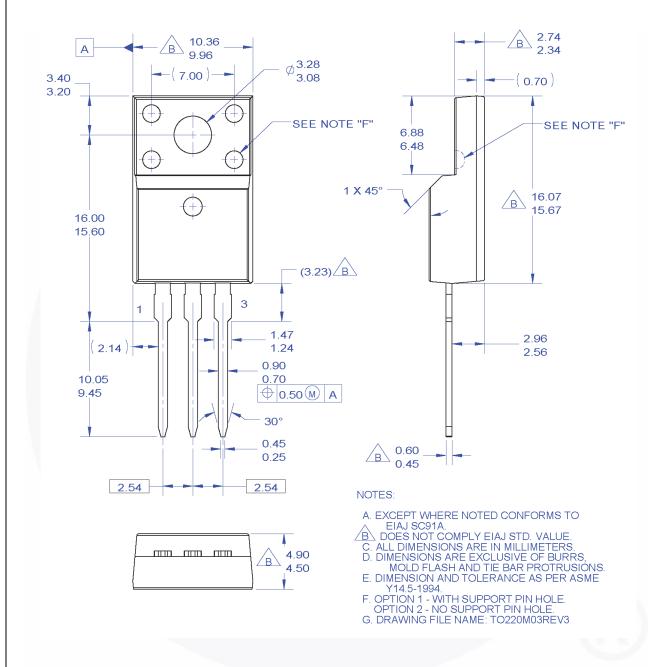


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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